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Serial No. N/A

INFORMATION DISCLOSURE STATEMENT

Applicants: Hisashi OHTANI et al.

Filing Date: July 20, 2001

Group Art Unit: 2814

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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*EXAMINER. Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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